

NS6130-10-1048

GALLIUM NITRIDE

Sputtering Target

Quick Facts

Product	:	Gallium Nitride Sputtering Target
Stock No	:	NS6130-10-1048
CAS	:	25617-97-4
Purity	:	99.99%
Molecular Formula	:	GaN

Technical Specification

Diameter	Thickness
50.8 mm \pm 1mm	3 mm \pm 0.5mm

GaN sputtering targets are valuable materials for the production of thin films with specific properties for various applications in the semiconductor and electronics industries. GaN sputtering targets have a range of properties, including high thermal stability, excellent electrical conductivity, and good optical properties. They are commonly used in the production of light-emitting diodes (LEDs), laser diodes, and power electronics, as well as in other electronic and optoelectronic applications.



* This image is for graphic purposes only and does not represent the actual product.

